

isc Silicon NPN Darlington Power Transistor

2SD1410

DESCRIPTION

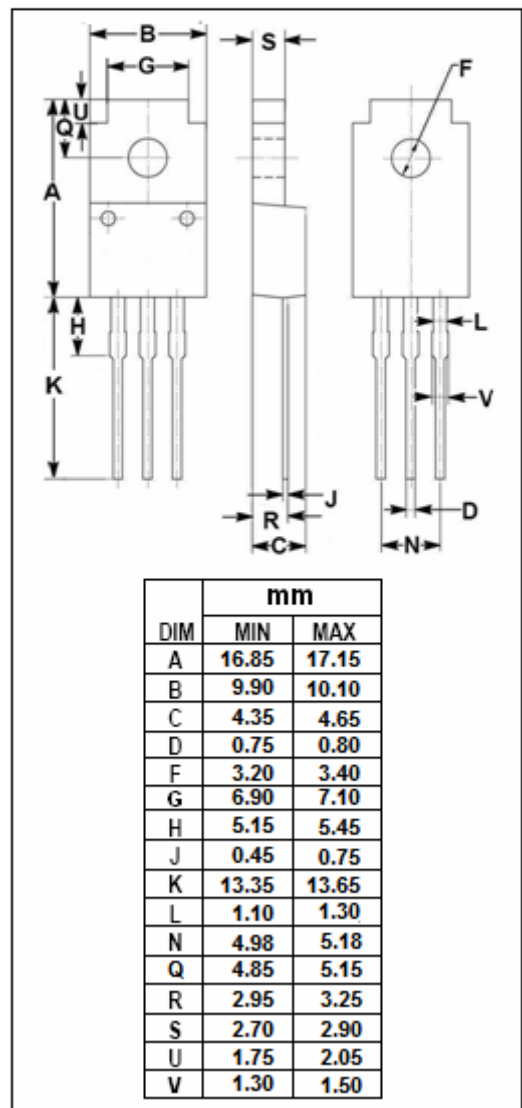
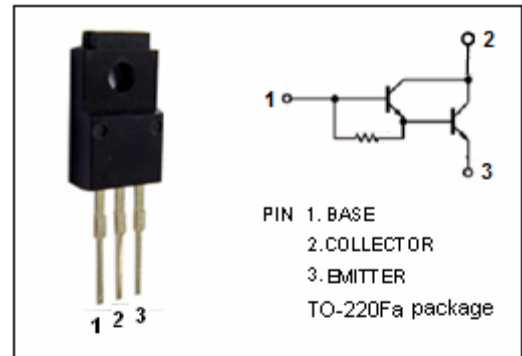
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 250V(\text{Min})$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 2.0V(\text{Max}) @ I_C = 4A$
- High DC Current Gain  
:  $h_{FE} = 2000(\text{Min}) @ I_C = 2A, V_{CE} = 2V$

APPLICATIONS

- Igniter applications
- High voltage switching applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	300	V
$V_{CEO}$	Collector-Emitter Voltage	250	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	6	A
$I_B$	Base Current-Continuous	1	A
$P_C$	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2.0	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$





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